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APPLICATION NO.	FI	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/073,751	02/09/2002		Arjun Kar Roy	01CON211P	4492
25700	7590	11/17/2003		EXAMINER	
FARJAMI			CHU, CHRIS C		
16148 SAND CANYON IRVINE, CA 92618				ART UNIT PAPER NUMI	
11(11(12), 0	***·**********************************			2815	

DATE MAILED: 11/17/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

*							
	Application N .	Applicant(s)					
	10/073,751	KAR ROY ET AL.					
Office Action Summary	Examiner	Art Unit					
	Chris C. Chu	2815					
The MAILING DATE of this communication Period for Reply	appears on the cover she t with the	e correspondence address					
A SHORTENED STATUTORY PERIOD FOR REL THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under be provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory per - Failure to reply within the set or extended period for reply will, by state - Any reply received by the Office later than three months after the may earned patent term adjustment. See 37 CFR 1.704(b). Status	N. R 1.136(a). In no event, however, may a reply be reply within the statutory minimum of thirty (30) and will apply and will expire SIX (6) MONTHS fratute, cause the application to become ABANDO	timely filed days will be considered timely. om the mailing date of this communication. NED (35 U.S.C. § 133).					
1) Responsive to communication(s) filed on 22	<u> 2 September 2003</u> .						
2a) This action is FINAL . 2b) ⊠ TI	This action is FINAL . 2b)⊠ This action is non-final.						
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Disposition of Claims							
4a) Of the above claim(s) is/are without 5) ☐ Claim(s) is/are allowed. 6) ☑ Claim(s) <u>1 - 5, 7 - 13 and 15 - 18</u> is/are rejee 7) ☐ Claim(s) is/are objected to.	☑ Claim(s) <u>1 - 5, 7 - 13 and 15 - 18</u> is/are rejected.						
Application Papers	a, o. 0.00.1011104a110111011101						
9) The specification is objected to by the Exam 10) The drawing(s) filed on is/are: a) a Applicant may not request that any objection to the Replacement drawing sheet(s) including the cortain the cortain of the	accepted or b) objected to by the drawing(s) be held in abeyance. Strection is required if the drawing(s) is	See 37 CFR 1.85(a). objected to. See 37 CFR 1.121(d).					
Priority under 35 U.S.C. §§ 119 and 120							
12) Acknowledgment is made of a claim for fore a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the papplication from the International Bur * See the attached detailed Office action for a 13) Acknowledgment is made of a claim for dome since a specific reference was included in the 37 CFR 1.78. a) The translation of the foreign language 14) Acknowledgment is made of a claim for dome reference was included in the first sentence of	ents have been received. ents have been received in Applic priority documents have been received (PCT Rule 17.2(a)). list of the certified copies not receivestic priority under 35 U.S.C. § 11 first sentence of the specification provisional application has been restic priority under 35 U.S.C. §§ 1	ation No ived in this National Stage ived. 9(e) (to a provisional application) or in an Application Data Sheet. eceived. 20 and/or 121 since a specific					
Attachment(s)							
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper Note	5) 🔲 Notice of Informa	ary (PTO-413) Paper No(s) Il Patent Application (PTO-152)					

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DETAILED ACTION

Request for Continued Examination

- 1. A request for continued examination (RCE) under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on September 22, 2003 has been entered. An action on the RCE follows.
- 2. Applicant's amendment filed on September 22, 2003 has been received and entered in the case.

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 4. Claims 1 5, 7 13 and 15 18 are rejected under 35 U.S.C. 102(b) as being anticipated by Zhao et al.

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Regarding claim 1, Zhao et al. discloses in Fig. 2L an integrated circuit chip comprising:

- a first interconnect metal layer (204);
- a first intermetallic dielectric layer (205) situated over said first interconnect metal layer;
- a metal resistor (220, at the left-side) situated over said first intermetallic dielectric layer;
- a dielectric cap layer (222) patterned on said metal resistor;
- a second intermetallic dielectric layer (224) formed over said dielectric cap layer and metal resistor;
- a second interconnect metal layer (234) over said second intermetallic dielectric
 layer;
- a first intermediate via (232, at the left-side) connected to a first terminal of said metal resistor, said first intermediate via being further connected to a first metal segment patterned in said second interconnect metal layer;
- a second intermediate via (232, at the middle) connected to a second terminal of a
 metal resistor, the second intermediate via being further connected to a second metal
 segment patterned in said second interconnect metal layer.

Regarding claims 2 and 11, Zhao et al. discloses in Fig. 2L and column 6, lines $27 \sim 32$ the metal resistor being tantalum nitride

Regarding claims 3 and 16, Zhao et al. discloses in Fig. 2L and column 4, lines $12 \sim 17$ the first interconnect metal layer (204) comprising aluminum.

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Regarding claims 4 and 12, Zhao et al. discloses in Fig. 2L and column 4, lines $18 \sim 38$ the first intermetallic dielectric layer comprising HDPCVD silicon dioxide.

Regarding claims 5 and 13, Zhao et al. discloses in Fig. 2L and column 4, lines $18 \sim 38$ the second intermetallic dielectric layer comprising undoped silica glass (HDPCVD SiO2 constitutes an undoped silica glass).

Regarding claims 7 and 15, Zhao et al. discloses in Fig. 2L and column 7, lines $17 \sim 20$ the dielectric cap layer comprising silicon nitride.

Regarding claims 8 and 17, Zhao et al. discloses in Fig. 2L and column 7, lines $17 \sim 20$ an oxide cap layer (222) situating between a metal resistor and a dielectric layer.

Regarding claims 9 and 18, Zhao et al. discloses in Fig. 2L and column 7, lines $17 \sim 20$ the oxide cap layer comprising PECVD silicon dioxide.

Regarding claim 10, Zhao et al. discloses in Fig. 2L an integrated circuit chip comprising:

- a first interconnect metal layer (204);
- a first intermetallic dielectric layer (205) situated over said first interconnect metal layer;
- a metal resistor (220, at the left-side) situated over said first intermetallic dielectric layer;
- a dielectric cap layer (222) patterned on said metal resistor;
- a second intermetallic dielectric layer (224) formed over said dielectric cap layer and metal resistor;
- a second interconnect metal layer (234) over said second intermetallic dielectric layer;

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a first intermediate via (232, at the left-side) connected to a first terminal of said

metal resistor;

a second intermediate via (232, at the middle) connected to a second terminal of the

metal resistor.

Response to Arguments

Applicant's arguments with respect to claims 1 and 10 have been considered but are moot 5.

in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Chris C. Chu whose telephone number is (703) 305-6194. The

examiner can normally be reached on M-F (10:30 - 7:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Tom Thomas can be reached on (703) 308-2772. The fax phone number for the

organization where this application or proceeding is assigned is (703) 308-7382.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 308-0956

Chris C. Chu

Examiner

PRIMARY EXAMINER

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